

IN THE SPECIFICATION:

**Please amend paragraph [0030] as follows:**

[0030] The radiation system comprises a source LA (*e.g.*, a UV laser or a plasma source) that produces a beam of radiation. This beam is fed into an illumination system (illuminator) IL, either directly or after being passed through conditioning means, such as a beam expander Ex, for example. The illuminator IL comprises adjusting means AM for setting the outer and/or inner radial extent (commonly referred to as ~~□-outer~~ σ-outer and ~~□-inner~~ σ-inner, respectively) of the intensity distribution in the beam. In addition, it will generally comprise various other components, such as an integrator IN and a condenser CO. In this way, the beam PB impinging on the mask MA has a desired uniformity and intensity distribution in its cross-section.

**Please amend paragraph [0034] as follows:**

[0034] Figure 2 shows a wafer W on a wafer table WT. Wafer marks WM3 and WM4 are provided on a first side (“front side”) of the wafer W and light can be reflected from these marks, as indicated by the arrows above WM3 and WM4, and used for alignment with marks on a mask in conjunction with an alignment system (not shown) which will be described later. Further wafer marks WM1 and WM2 are provided on the second side (“back side”) of the wafer W. An optical system is built into the wafer table WT for providing optical access to the wafer marks WM1, WM2 on the back side of the wafer W. The optical system comprises a pair of arms 10A, 10B. Each arm consists of two mirrors, 12, 14 and two lenses 16, 18. The mirrors 12, 14 in each arm are inclined such that the sum of the angles that they make with the horizontal is ~~90□~~ 90°. In this way, a beam of light impinging vertically on one of the mirrors will remain vertical when reflected off the other mirror.